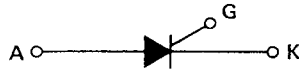


MCR1906-1 thru MCR1906-8



REVERSE BLOCKING TRIODE THYRISTORS

These devices are glassivated planar construction designed for applications in control systems and sensing circuits where low-level gating and holding characteristics are necessary.

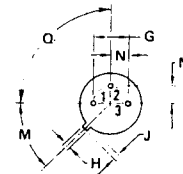
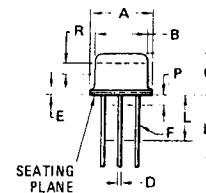
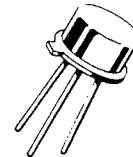
- Low-Level Gate Characteristics –
 $I_{GT} = 1.0 \text{ mA (Max) @ } T_C = 25^\circ\text{C}$
- Low Holding Current – $I_H = 5.0 \text{ mA (Max) @ } T_C = 25^\circ\text{C}$
- Glass-to-Metal Bond for Maximum Hermetic Seal

MAXIMUM RATINGS ($T_J = 100^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Repetitive Peak Reverse Blocking Voltage	V_{RRM}	25 50 100 200 300 400 500 600	Volts
MCR1906-1			
MCR1906-2			
MCR1906-3			
MCR1906-4			
MCR1906-5			
MCR1906-6			
MCR1906-7 MCR1906-8			
RMS On-State Current (All Conduction Angles)	$I_T(\text{RMS})$	1.6	Amp
Peak Non-Repetitive Surge Current (One Cycle, 60 Hz, $T_J = -40$ to $+110^\circ\text{C}$) Preceded and followed by rated current and voltage	I_{TSM}	15	Amp
Peak Gate Power	P_{GM}	0.1	Watt
Average Gate Power	$P_{GF(AV)}$	0.01	Watt
Peak Gate Current	I_{GM}	0.1	Amp
Peak Gate Voltage	V_{GM}	6.0	Volt
Operating Junction Temperature Range	T_J	-65 to +110	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Lead Solder Temperature ($> 1/16''$ From Case, 10 s max.)	-	+230	$^\circ\text{C}$

SILICON CONTROLLED RECTIFIERS

1.6 AMPERES RMS
25 thru 400 VOLTS



STYLE 3:
PIN 1. CATHODE
2. GATE
3. ANODE (CONNECTED TO CASE)

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.89	9.40	0.350	0.370
B	8.00	8.51	0.315	0.335
C	6.10	6.60	0.240	0.260
D	0.406	0.533	0.016	0.021
E	0.229	3.18	0.009	0.125
F	0.406	0.483	0.016	0.019
G	4.83	5.33	0.190	0.210
H	0.711	0.864	0.028	0.034
J	0.737	1.02	0.029	0.040
K	12.70	-	0.500	-
L	6.35	-	0.250	-
M	45° NOM	-	45° NOM	-
P	-	1.27	-	0.050
Q	90° NOM	-	90° NOM	-
R	2.54	-	0.100	-

All JEDEC dimensions and notes apply

MCR1906-1 thru MCR1906-8

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Forward Blocking Voltage ($R_{GK} = 1000 \text{ Ohms}$)	V_{DRM}	MCR1906-1 25	—	—	Volt
MCR1906-2 50		—	—		
MCR1906-3 100		—	—		
MCR1906-4 200		—	—		
MCR1906-5 300		—	—		
MCR1906-6 400		—	—		
MCR1906-7 500		—	—		
MCR1906-8 600		—	—		
Peak Forward Blocking Current (Rated V_{DRM} , $R_{GK} = 1000 \text{ Ohms}$, $T_J = 110^\circ\text{C}$)	I_{DRM}	—	—	500	μA
Peak Reverse Blocking Current (Rated V_{RRM} , $R_{GK} = 1000 \text{ Ohms}$, $T_J = 110^\circ\text{C}$)	I_{RRM}	—	—	500	μA
Peak On-State Voltage (Pulsed, 1.0 ms max, Duty Cycle $\leq 1.0\%$) ($I_F = 1.0 \text{ A}$ dc peak)	V_{TM}	—	—	1.75	Volt
Gate Trigger Current (Continuous dc) ($V_{AK} = 7.0 \text{ V}$, $R_L = 100 \text{ ohms}$)	I_{GT}	—	—	1.0	mAdc
Gate Trigger Voltage (Continuous dc) ($V_{AK} = 7.0 \text{ V}$, $R_L = 100 \text{ ohms}$) ($V_{AK} = \text{Rated } V_{DRM}$, $R_L = 100 \text{ ohms}$, $R_{GK} = 1000 \text{ Ohms}$, $T_J = 110^\circ\text{C}$)	V_{GT}	—	—	1.0	Volt
		0.1	—	—	
Holding Current ($V_{AK} = 7.0 \text{ V}$, $R_{GK} = 1000 \text{ ohms}$)	I_H	—	—	5.0	mA
Turn-On Time ($I_{GT} = 10 \text{ mA}$, $I_F = 1.0 \text{ A}$) ($I_{GT} = 20 \text{ mA}$, $I_F = 1.0 \text{ A}$)	t_{gt}	—	0.8	—	μs
		—	0.6	—	
Turn-Off Time ($I_F = 1.0 \text{ A}$, $I_R = 1.0 \text{ A}$, $dv/dt = 20 \text{ V}/\mu\text{s}$, $T_J = 110^\circ\text{C}$)	t_d	—	10	—	μs